



SANYO SEMICONDUCTOR

2SD621

2SD621 NPN Triple Diffused Mesa Type Silicon Transistor
For H-Deflection Output with High Voltage

Absolute Maximum Ratings at Ta=25°C

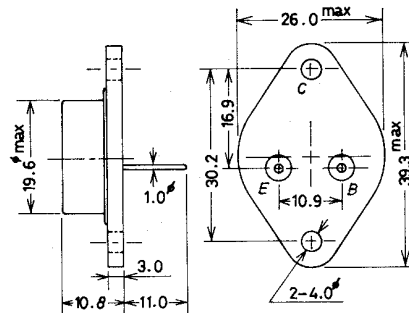
Collector to Base Voltage	V _{CB0}	2500 V
Collector to Emitter Voltage	V _{CE0}	900 V
Emitter to Base Voltage	V _{EB0}	6 V
Collector Current	I _C	3 A
Peak Collector Current	i _{cp}	7 A
Collector Dissipation	P _C	50 W
Junction Temperature	T _j	150 °C
Storage Temperature	T _{stg}	-40 to +150 °C

T_c=25°C

Electrical Characteristics at Ta=25°C

		min	typ	max	unit
Collector Cutoff Current	I _{CBO} (1) V _{CB} =1000V, I _E =0			50	uA
	I _{CBO} (2) V _{CB} =2500V, I _E =0			1.0	mA
Emitter Cutoff Current	I _{EBO} V _{EB} =6V, I _C =0			1.0	mA
Collector Cutoff Current	I _{CEO} V _{CE} =900V, I _B =0			10	mA
DC Current Gain	h _{FE} V _{CE} =10V, I _C =1.5A	3		15	
C-E Saturation Voltage	V _{CE} (sat) I _C =1.5A, I _B =0.5A			10	V
B-E Saturation Voltage	V _{BE} (sat) I _C =1.5A, I _B =0.5A			1.25	V
Fall Time	t _f i _{cp} =1.5A			1.0	us

Case Outline (unit:mm)



EIAJ. TC-3, TB-3
JEDEC. TO-3

C. Collector
E. Emitter
B. Base